MBR0540T1, MBR0540T3

Surface Mount Schottky Power Rectifier

SOD−123 Power Surface Mount Package

The Schottky Power Rectifier employs the Schottky Barrier principle with a barrier metal that produces optimal forward voltage drop−reverse current tradeoff. Ideally suited for low voltage, high frequency rectification, or as a free wheeling and polarity protection diodes in surface mount applications where compact size and weight are critical to the system. This package provides an alternative to the leadless 34 MELF style package.

Features

- Guardring for Stress Protection
- Very Low Forward Voltage
- Epoxy Meets UL 94 V−0 @ 0.125 in
- Package Designed for Optimal Automated Board Assembly
- Pb−Free Packages are Available

Mechanical Characteristics

- Reel Options: 3,000 per 7 inch reel/8 mm tape
- Reel Options: 10,000 per 13 inch reel/8 mm tape
- Device Marking: SF
- Polarity Designator: Cathode Band
- Weight: 11.7 mg (approximately)
- Case: Epoxy Molded
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead and Mounting Surface Temperature for Soldering Purposes: 260°C max. for 10 Seconds

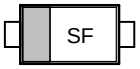
ON Semiconductor®

http://onsemi.com

SCHOTTKY BARRIER RECTIFIER 0.5 AMPERES, 40 VOLTS

SOD−123
CASE 425
STYLE 1

MARKING DIAGRAM



SF= Device Code

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping†
MBR0540T1	SOD−123	3000/Tape & Reel
MBR0540T1G	SOD−123 (Pb−Free)	3000/Tape & Reel
MBR0540T3	SOD−123	10,000/Tape & Reel
MBR0540T3G	SOD−123 (Pb−Free)	10,000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	40	V
Average Rectified Forward Current (At Rated V_R, T_C = 115°C)	I_O	0.5	A
Peak Repetitive Forward Current (At Rated V_R, Square Wave, 20 kHz, T_C = 115°C)	I_{FRM}	1.0	A
Non−Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions Halfwave, Single Phase, 60 Hz)	I_{FSM}	5.5	A
Storage/Operating Case Temperature Range	T_{stg}, T_C	−55 to +150	°C
Operating Junction Temperature	T_J	−55 to +150	°C
Voltage Rate of Change (Rated V_R, T_J = 25°C)	dv/dt	1000	V/μs

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Rating	Symbol	Value	Unit
Thermal Resistance − Junction−to−Lead (Note 1) Thermal Resistance − Junction−to−Ambient (Note 2)	R_{tjl} R_{tja}	118 206	°C/W

ELECTRICAL CHARACTERISTICS

Maximum Instantaneous Forward Voltage (Note 3)	v_F	**T_J = 25°C**	**T_J = 100°C**	V
(i_F = 0.5 A) (i_F = 1 A)		0.51 0.62	0.46 0.61	
Maximum Instantaneous Reverse Current (Note 3)	I_R	**T_J = 25°C**	**T_J = 100°C**	μA
(V_R = 40 V) (V_R = 20 V)		20 10	13,000 5,000	

1. Mounted with minimum recommended pad size, PC Board FR4.
2. 1 inch square pad size (1 X 0.5 inch for each lead) on FR4 board.
3. Pulse Test: Pulse Width ≤ 250 μs, Duty Cycle ≤ 2.0%.

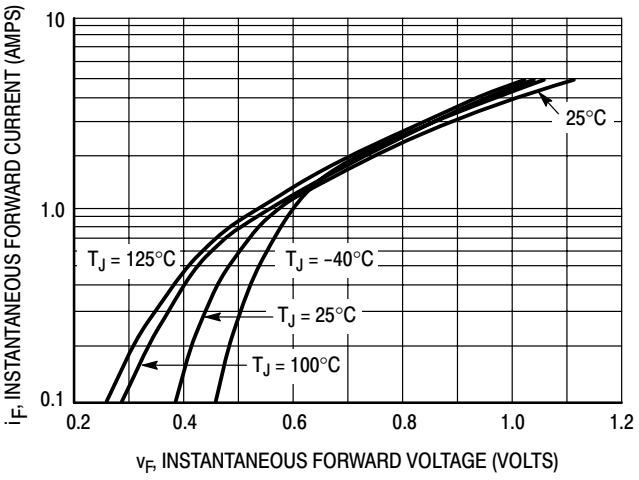


Figure 1. Typical Forward Voltage

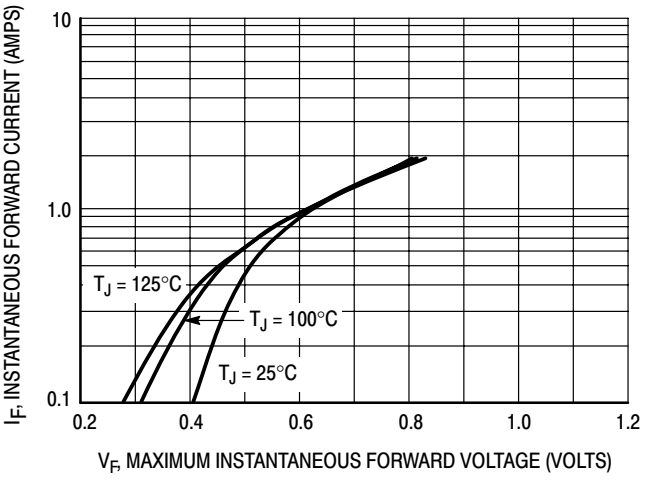


Figure 2. Maximum Forward Voltage

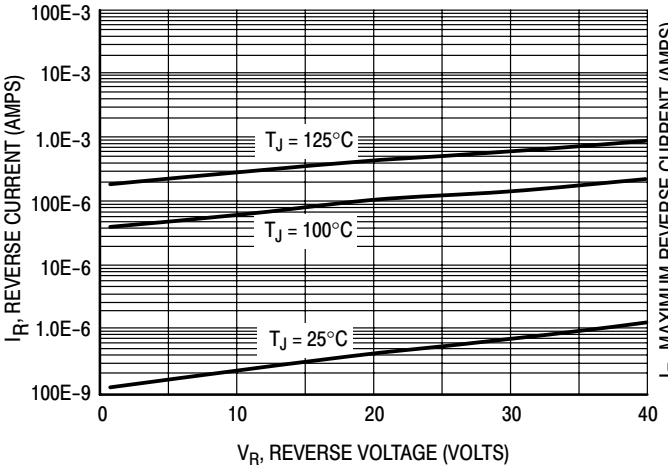


Figure 3. Typical Reverse Current

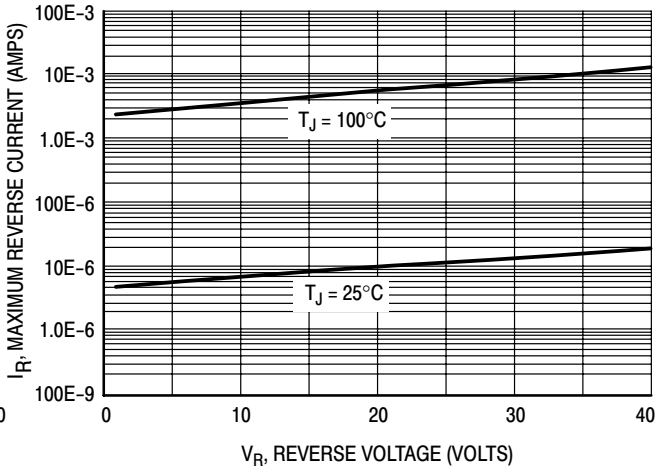


Figure 4. Maximum Reverse Current

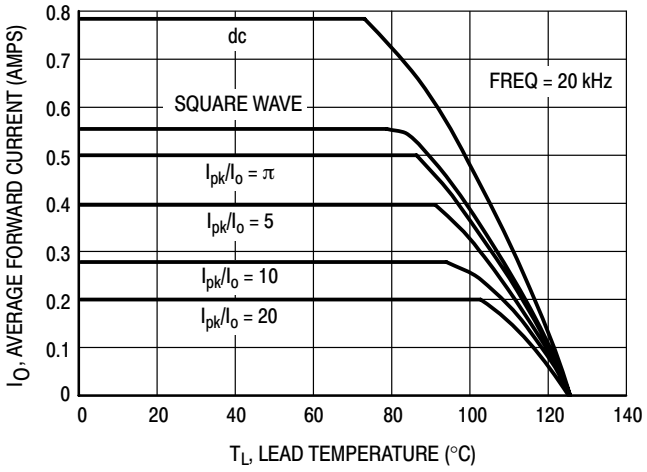


Figure 5. Current Derating

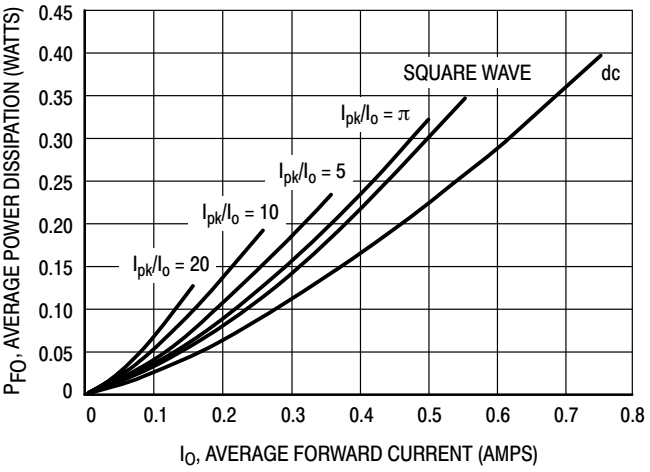


Figure 6. Forward Power Dissipation

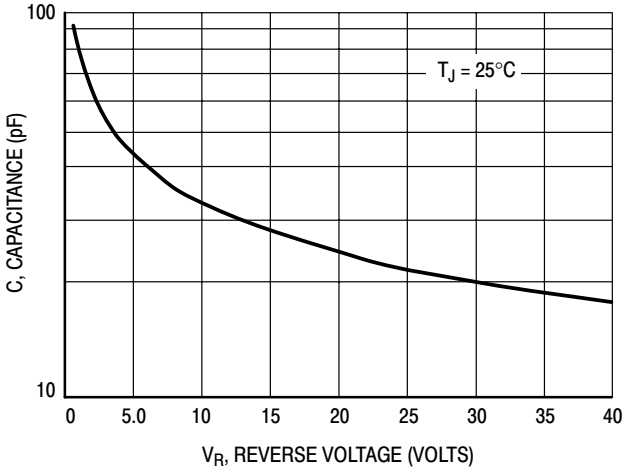


Figure 7. Capacitance

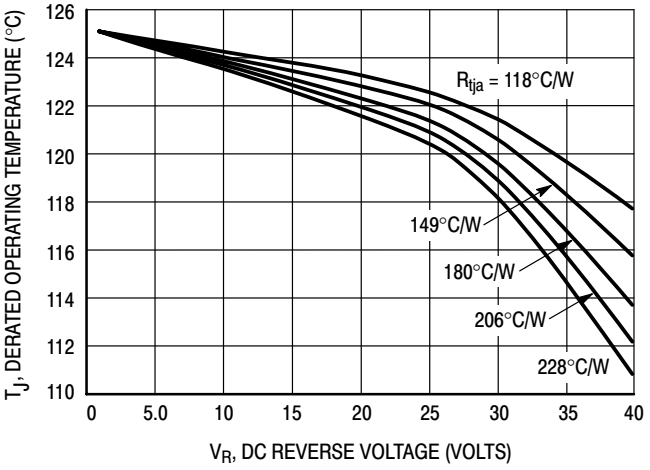


Figure 8. Typical Operating Temperature Derating*

* Reverse power dissipation and the possibility of thermal runaway must be considered when operating this device under any reverse voltage conditions. Calculations of T_J therefore must include forward and reverse power effects. The allowable operating T_J may be calculated from the equation: $T_J = T_{Jmax} - r(t)(Pf + Pr)$ where

r(t) = thermal impedance under given conditions,
Pf = forward power dissipation, and
Pr = reverse power dissipation

This graph displays the derated allowable T_J due to reverse bias under DC conditions only and is calculated as $T_J = T_{Jmax} - r(t)Pr$, where r(t) = Rthja. For other power applications further calculations must be performed.

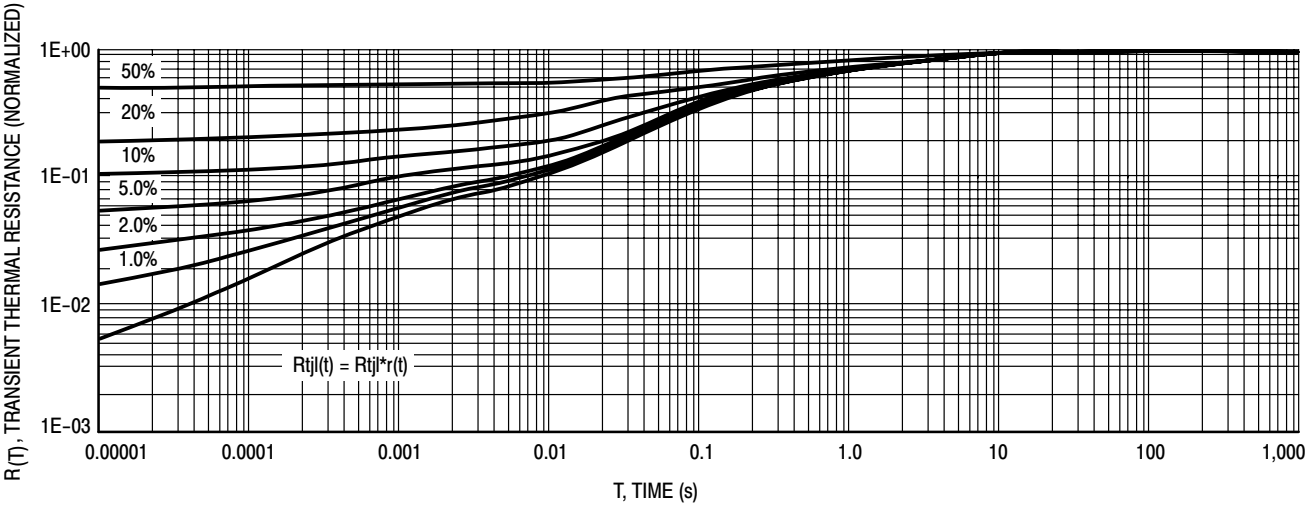


Figure 9. Thermal Response Junction to Lead

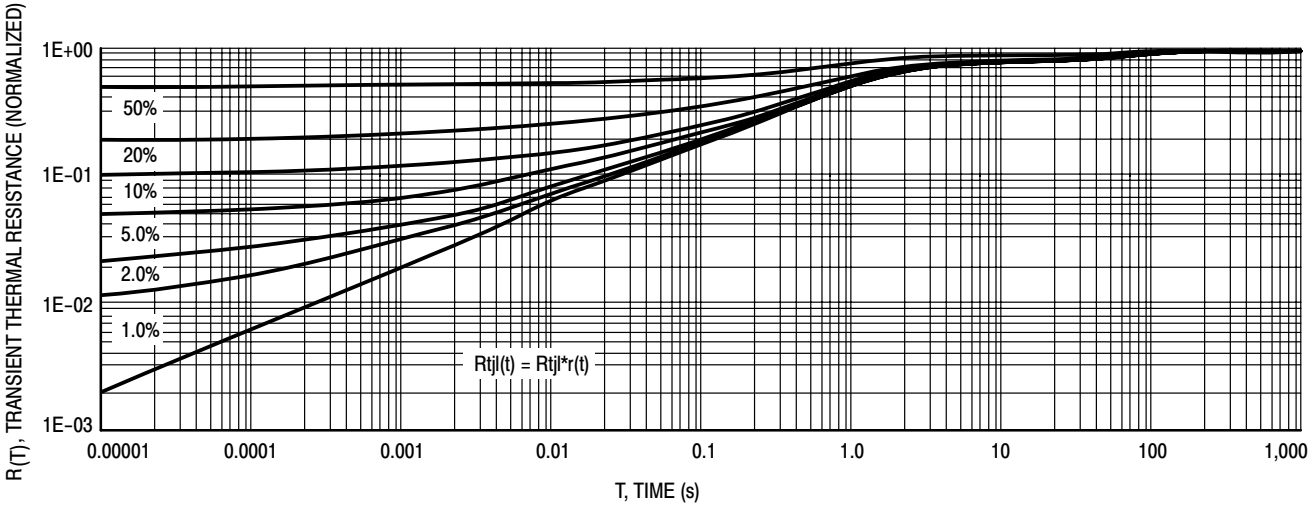
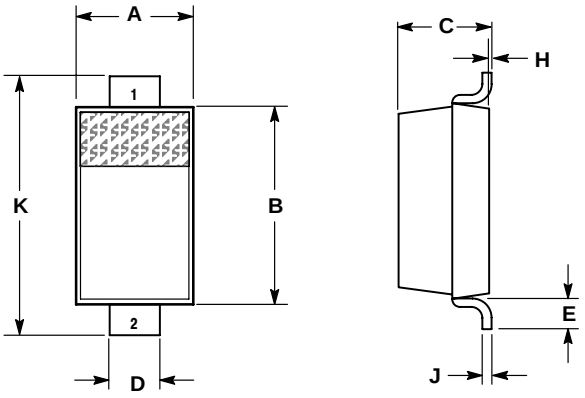


Figure 10. Thermal Response Junction to Ambient

PACKAGE DIMENSIONS

SOD−123
PLASTIC
CASE 425−04
ISSUE C

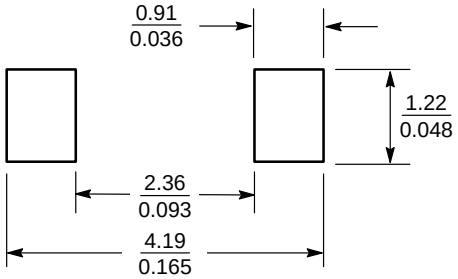


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.055	0.071	1.40	1.80
B	0.100	0.112	2.55	2.85
C	0.037	0.053	0.95	1.35
D	0.020	0.028	0.50	0.70
E	0.004	---	0.25	---
H	0.000	0.004	0.00	0.10
J	---	0.006	---	0.15
K	0.140	0.152	3.55	3.85

STYLE 1:
PIN 1. CATHODE
2. ANODE

SOLDERING FOOTPRINT*



SCALE 10:1 $\left(\frac{\text{mm}}{\text{inches}}\right)$

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

MBR0540T1/D